

**ECE 531**  
**Microelectronics**  
**Assignment 6**

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**101266059**

## Question 1:

Here the power rails are at the same relative location and the gates are arranged side by side.

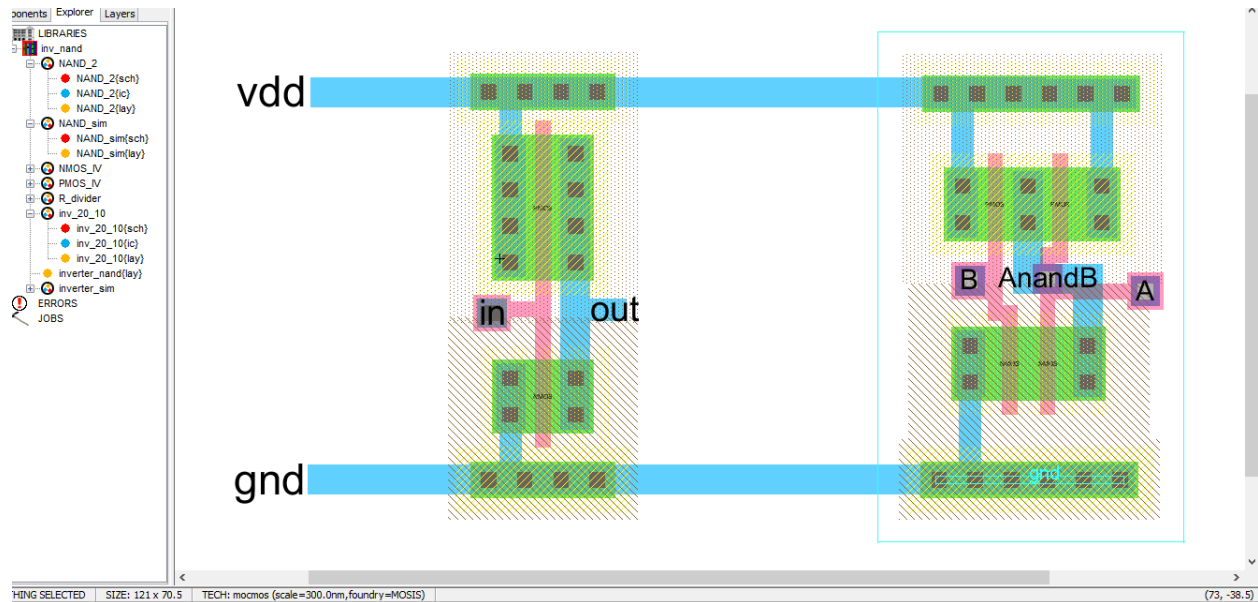


Figure 1: Electric Layout of the inverter and the nand gate.

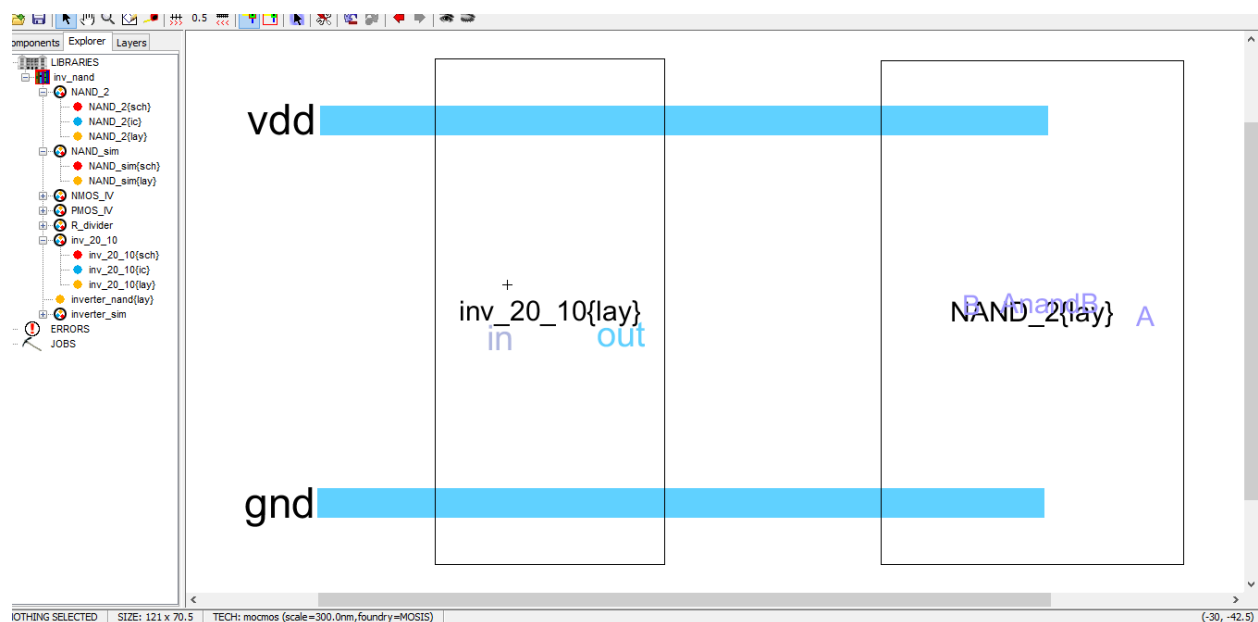


Figure 2: Electric Layout of the inverter and the nand gate.

## Question 2:

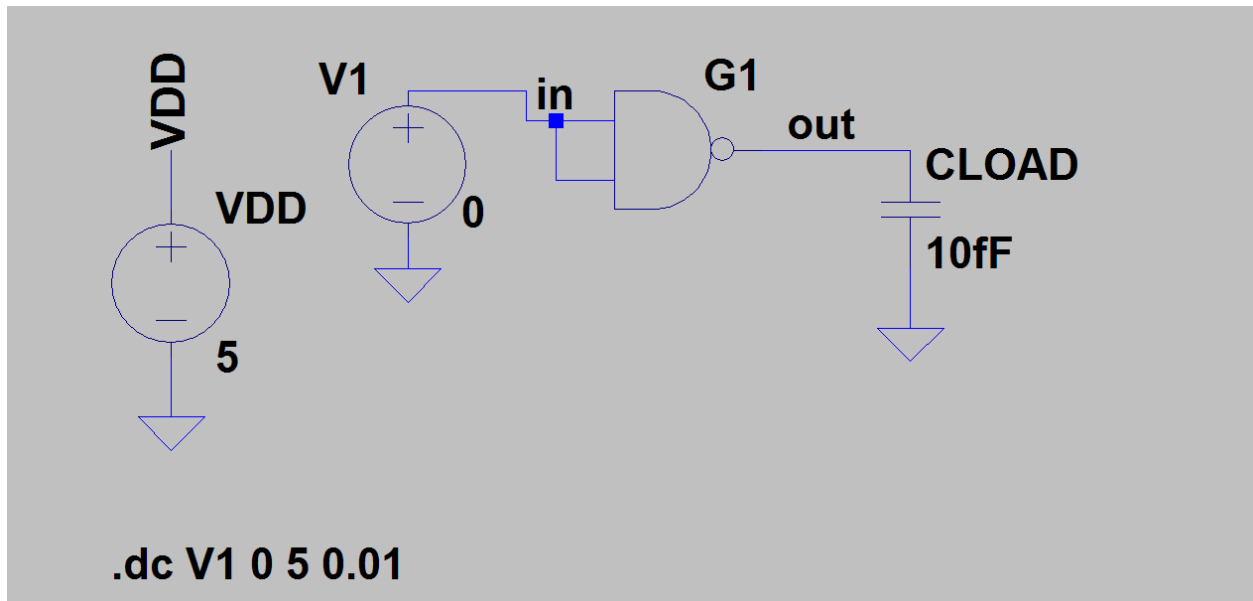


Figure 3: Equivalent circuit of the nand gate

```
vdd vdd 0 dc 5
vin in 0 dc 0 pulse 0 5 10n 1n
cload out 0 250fF
.tran 0 40n
.include C:\Electric\C5_models.txt
```

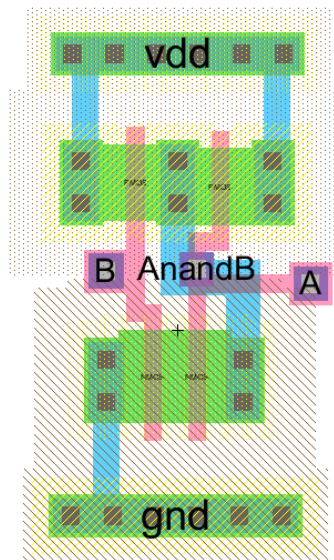


Figure 4: NAND gate in Electric Layout

The nand gate is designed in the Electric to get the parasitic parameters. Now these parameters kept in the LTSpice PMOS and NMOS.

```

*** SPICE deck for cell NAND_2{lay} from library tutorial_4
*** Created on Thu Jan 07, 2010 18:59:18
*** Last revised on Thu Mar 19, 2015 17:29:15
*** Written on Thu Mar 19, 2015 17:29:22 by Electric ULSI Design System,
*** version 9.05
*** Layout tech: mocmos, foundry MOSIS
*** UC SPICE *** , MIN_RESIST 4.0, MIN_CAPAC 0.1FF

*** TOP LEVEL CELL: NAND_2{lay}
Mnmos@0 net@7 B gnd gnd NMOS L=0.6U W=3.3U AS=20.07P AD=1.912P PS=31.8U
+PD=4.95U
Mnmos@1 AnandB A net@7 gnd NMOS L=0.6U W=3.3U AS=1.912P AD=4.5P PS=4.95U
+PD=7.2U
Mpmos@0 vdd B AnandB vdd PMOS L=0.6U W=2.7U AS=4.5P AD=13.579P PS=7.2U
+PD=21.225U
Mpmos@1 AnandB A vdd vdd PMOS L=0.6U W=2.7U AS=13.579P AD=4.5P PS=21.225U
+PD=7.2U

* Spice Code nodes in cell cell 'NAND_2{lay}'
vdd vdd 0 dc 5
vin in 0 dc 0 pulse 0 5 10n 1n
cload out 0 250FF
.tran 0 40n
.include C:\Electric\C5_models.txt
.END

```

Figure 5: Electric output

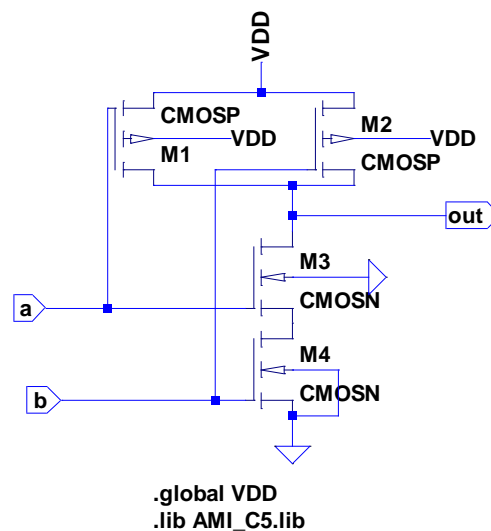


Figure 6: NAND gate LTSpice circuit

```
SPICE Netlist: E:\Jan_2015\Microelectronic systems\Assignment_6\problem_2\spice_na...
* E:\Jan_2015\Microelectronic systems\Assignment_6\problem_2\spice_nand\nand.as
M1 out a VDD VDD CMOSP l=0.6u w=2.7u ad=4.5P as=13.579P pd=7.2U ps=21.225U
M2 VDD b out VDD CMOSP l=0.6u w=2.7u ad=13.579P as=4.5P pd=21.225U ps=21.225U
M3 out a P001 0 CMOSN l=0.6u w=3.3u ad=4.5P as=1.912P pd=7.2U ps=4.95U
M4 P001 b 0 0 CMOSN l=0.6u w=3.3u ad=1.912P as=20.07P pd=4.95U ps=31.8U
.model NMOS NMOS
.model PMOS PMOS
.lib D:\LTSpice\lib\cmp\standard.mos
.global VDD
.lib AMI_C5.lib
.backanno
.end
```

Figure 7: Spicie Netlist of the Nand gate

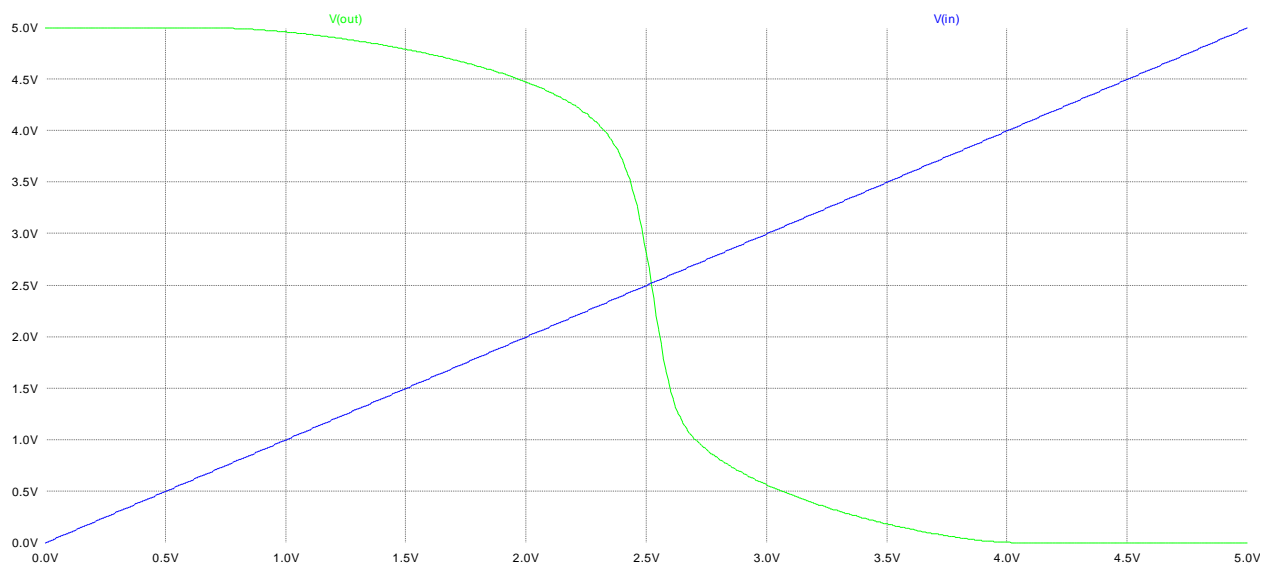


Figure 8: Spice output for the modified nand gate

Switch point = 2.5191131V.

Hence point

**Question 3:**

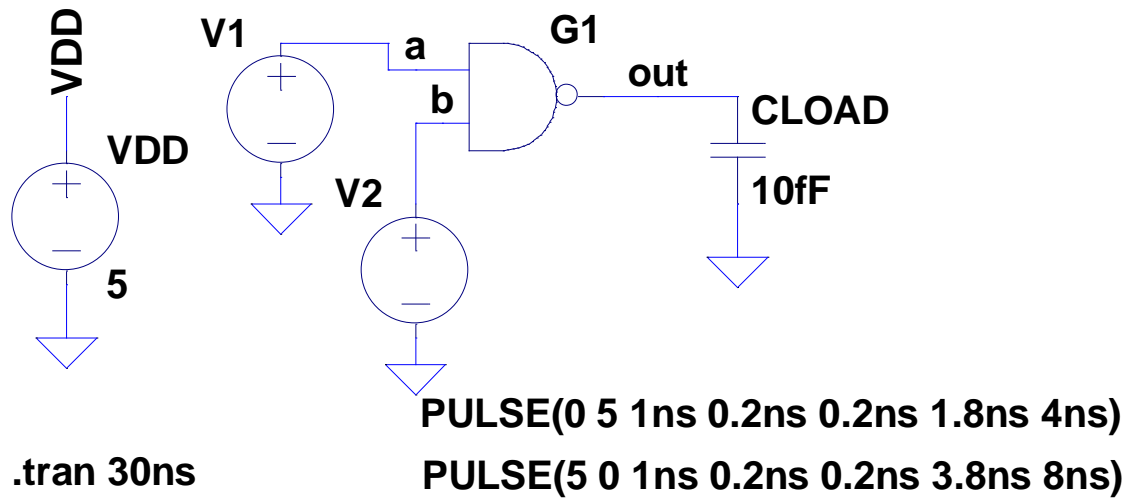


Figure 9: Equivalent circuit of the nand gate

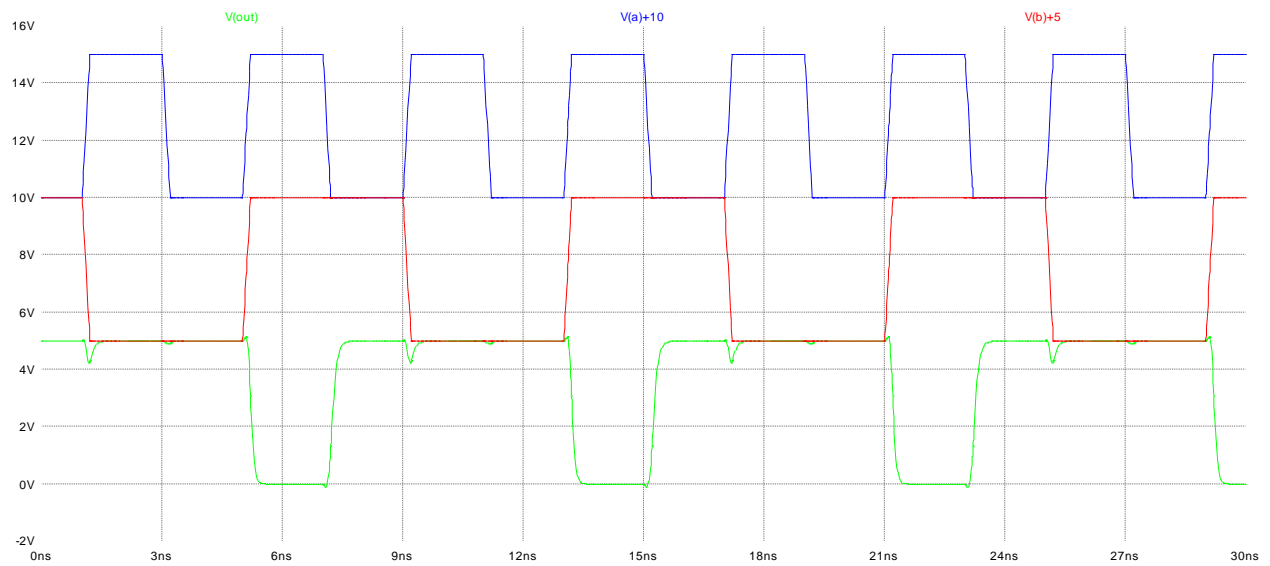
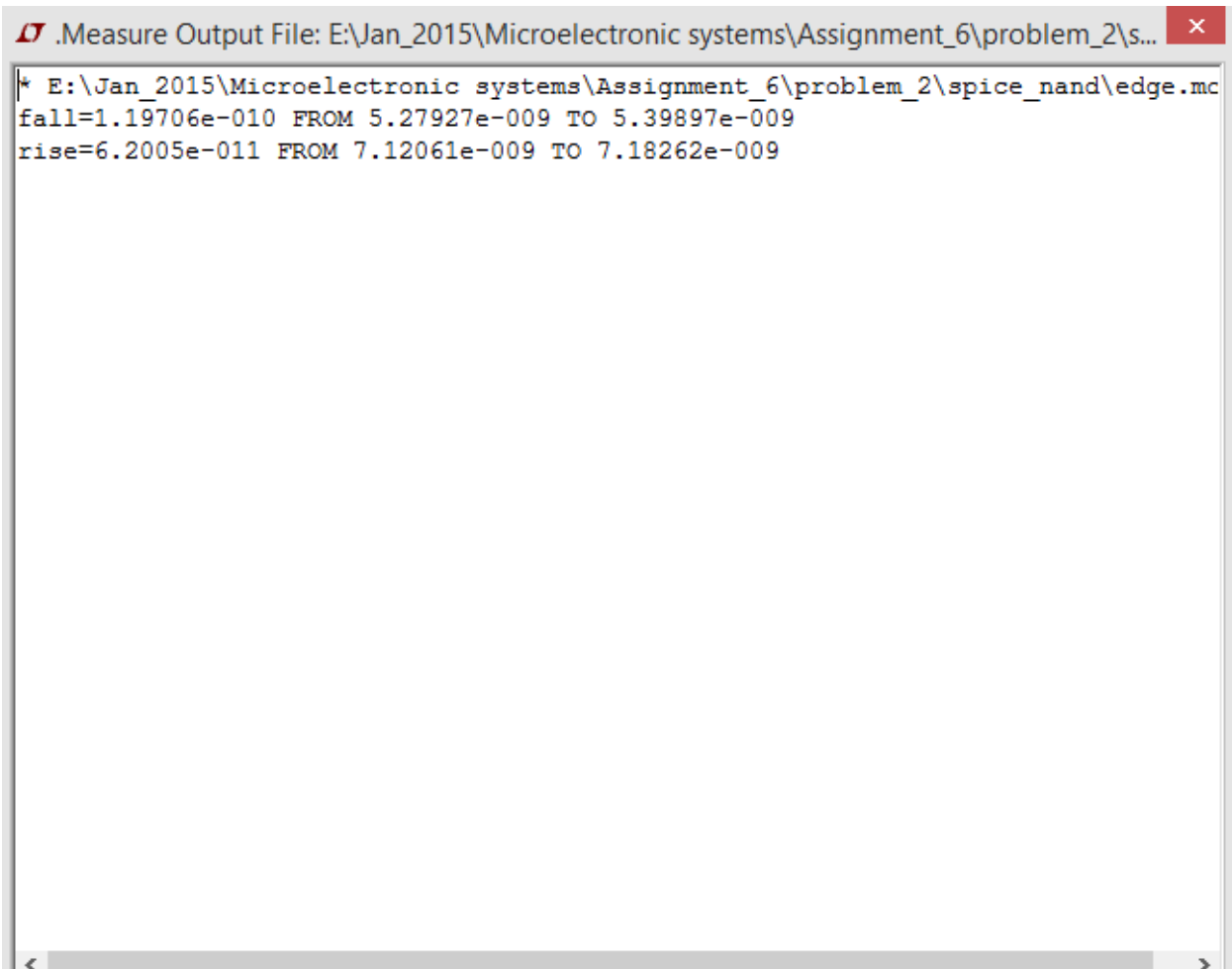


Figure 10: LTSpice simulation of the above circuit



The image shows a screenshot of a SPICE simulation output window. The title bar indicates the file path: ".Measure Output File: E:\Jan\_2015\Microelectronic systems\Assignment\_6\problem\_2\s...". The main text area contains the following information:

```
* E:\Jan_2015\Microelectronic systems\Assignment_6\problem_2\spice_nand\edge.mc  
fall=1.19706e-010 FROM 5.27927e-009 TO 5.39897e-009  
rise=6.2005e-011 FROM 7.12061e-009 TO 7.18262e-009
```

The output displays the fall and rise times of a signal. The fall time is 1.19706e-010 seconds, occurring between 5.27927e-009 and 5.39897e-009 seconds. The rise time is 6.2005e-011 seconds, occurring between 7.12061e-009 and 7.18262e-009 seconds.

Figure 11: Rise and fall time of the above circuit

## Parasitic parameters

```

*** SPICE deck for cell NAND_2{lay} from library tutorial_4
*** Created on Thu Jan 07, 2010 18:59:18
*** Last revised on Thu Mar 19, 2015 17:29:15
*** Written on Thu Mar 19, 2015 17:29:22 by Electric VLSI Design System,
*** version 9.05
*** Layout tech: mocomos, foundry MOSIS
*** UC SPICE *** , MIN_RESIST 4.0, MIN_CAPAC 0.1FF

*** TOP LEVEL CELL: NAND_2{lay}
Mnmos@0 net@7 B gnd gnd NMOS L=0.6U W=3.3U AS=20.07P AD=1.912P PS=31.8U
+PD=4.95U
Mnmos@1 AnandB A net@7 gnd NMOS L=0.6U W=3.3U AS=1.912P AD=4.5P PS=4.95U
+PD=7.2U
Mpmos@0 vdd B AnandB vdd PMOS L=0.6U W=2.7U AS=4.5P AD=13.579P PS=7.2U
+PD=21.225U
Mpmos@1 AnandB A vdd vdd PMOS L=0.6U W=2.7U AS=13.579P AD=4.5P PS=21.225U
+PD=7.2U

* Spice Code nodes in cell cell 'NAND_2{lay}'
vdd vdd 0 dc 5
vin in 0 dc 0 pulse 0 5 10n 1n
cload out 0 250FF
.tran 0 40n
.include C:\Electric\G5_models.txt
.END

```

Figure 12: Parasitic parameters of the nand gate

### Question 4:

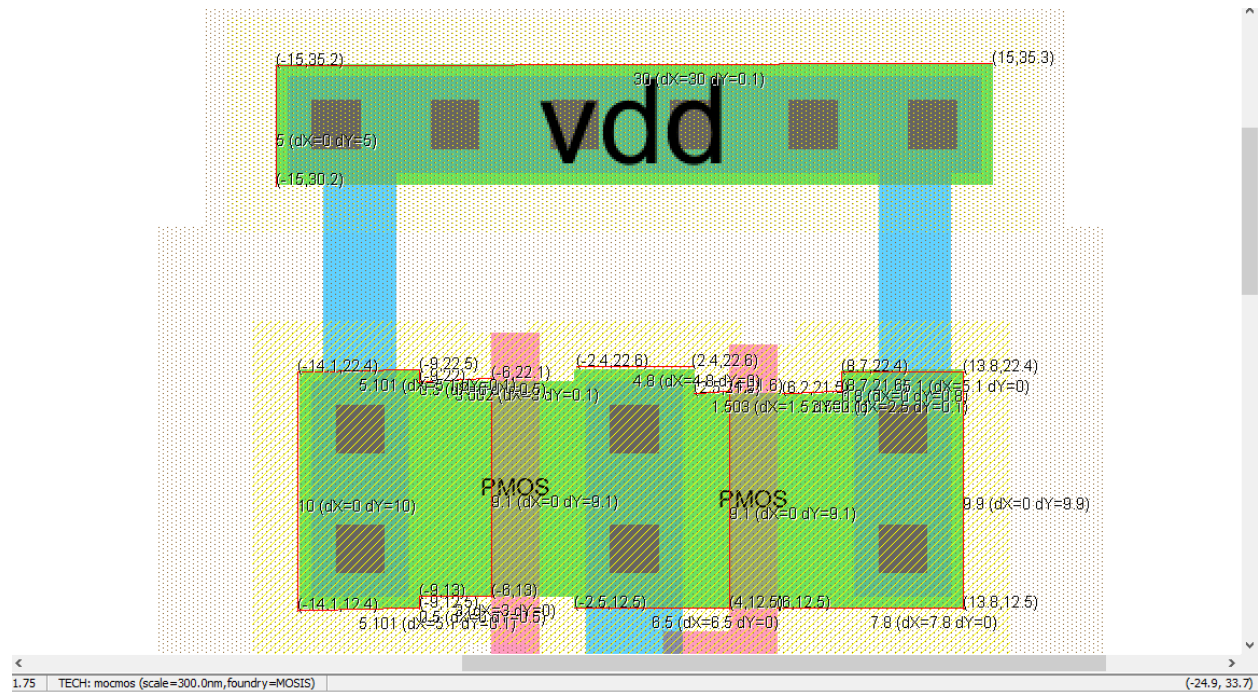




Figure 13: PMOS electric layout of NAND gate

Here  $\lambda = 0.3$

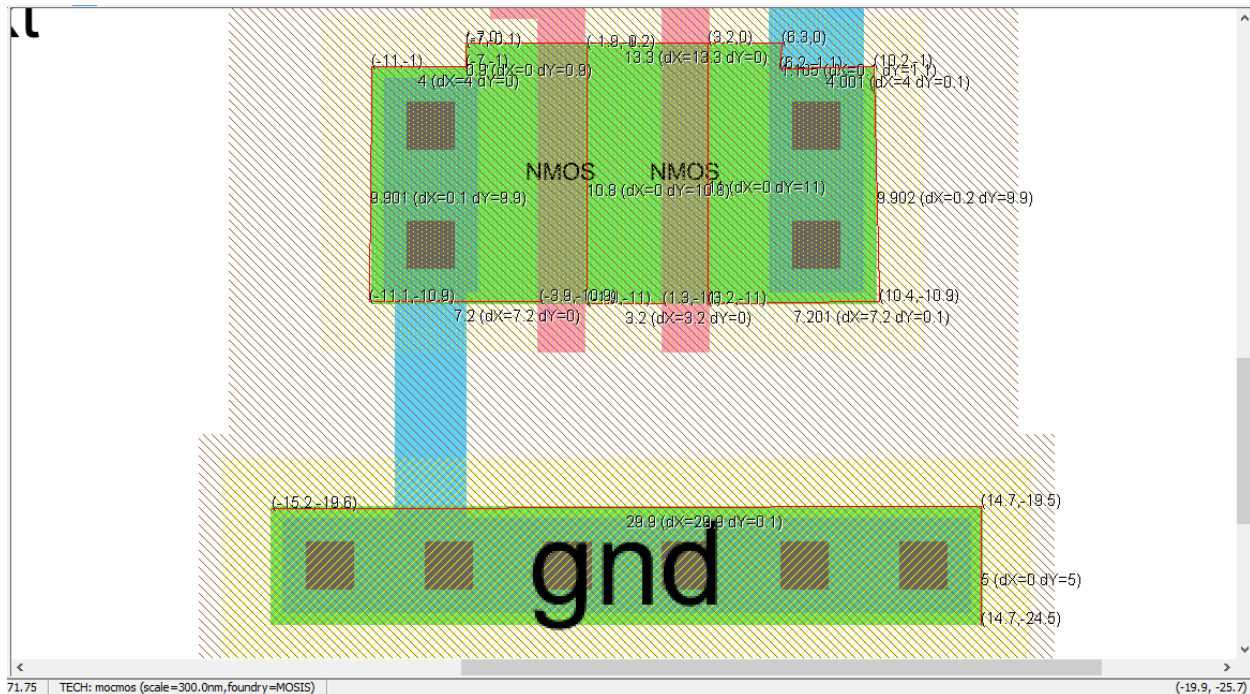


Figure 14: PMOS and NMOS Electric layout of NAND gate

#### PMOS 1:

$$\text{Area of Vdd} = 5 * 30 * \lambda^2 = 13.5 \text{ p}$$

$$\text{Source Area} = 10 * 5 * \lambda^2 + 3 * 9 * \lambda^2 = 4.5 + 2.45 = 6.93 \text{ p}$$

$$\text{Drain of PMOS 2} = 9 * 2.7 * \lambda^2 + 5 * 10 * \lambda^2 = 6.687 \text{ p}$$

$$\text{Area of source } \mathbf{AS} = 13.5 \text{ p}$$

$$\text{Area of drain} = 9 * 1 * \lambda^2 + 5 * 10 * \lambda^2 + 1.5 * 9 * \lambda^2 + 11 * 3 * \lambda^2 + 10 * 4 * \lambda^2 = 4.5 \text{ p}$$

$$\text{Area of Drain} = \mathbf{AD} = 4.5 \text{ p.}$$

$$\text{Perimeter of drain } \mathbf{PD} = (1.6 + 0.6 + 5 + 1 + 1.3 + 6.6 + 0.5 + 1.5 + 3 + 1 + 3.9 + 10 + 7 + 11) * \lambda / 3 = 24.3 * \lambda = 7.2 \text{ u}$$

$$\text{Perimeter of source} = \mathbf{PS} = (9 + 3 + 0.5 + 5 + 10 + 5 + 0.5 + 3 + 7 + 9 + 1 + 5 + 10 + 7.5) * \lambda / 2 = 21.2 \text{ u}$$

#### PMOS 0:

$$\text{Perimeter of drain } \mathbf{PD} = (9 + 3 + 0.5 + 5 + 10 + 5 + 0.5 + 3 + 7 + 9 + 1 + 5 + 10 + 7.5) * \lambda / 2 = 21.2 \text{ u}$$

Perimeter of source = **PS** =  $(1.6 + 0.6 + 5 + 1 + 1.3 + 6.6 + 0.5 + 1.5 + 3 + 1 + 3.9 + 10 + 7 + 11) * \lambda / 3 = 24.3 * \lambda = 7.2 \text{ u}$

Area of source **AS** = 4.5 p

Area of Drain = **AD** = 13.5 p

#### NMOS 1:

Perimeter of source **PS** =  $(3 + 1 + 4 + 10 + 7 + 11 + 70) * \lambda / 2 = 31.6 \text{ u}$

Area of Drain **AD** =  $(3.5 * 11) * \lambda * \lambda / 2 = 1.74 \text{ p}$

Area of Source **AS** =  $3 * 11 * \lambda^2 + 4 * 10 * \lambda^2 + 30 * 5 * \lambda^2 = 20.07 \text{ p}$

Perimeter of drain **PD** =  $(3.5 + 11) * 2 / 2 * \lambda = 4.4 \text{ u}$

Which is nearly equal to 4.9 u

#### NMOS 2:

Area of source **AS** =  $(3.5 * 11) * \lambda * \lambda / 2 = 1.74 \text{ p}$

Area of Drain **AD** =  $9 * 1 * \lambda^2 + 5 * 10 * \lambda^2 + 1.5 * 9 * \lambda^2 + 11 * 3 * \lambda^2 + 10 * 4 * \lambda^2 = 4.5 \text{ p}$

Perimeter of source **PS** =  $(3.5 + 11) * 2 / 2 * \lambda = 4.4 \text{ u}$

Perimeter of drain = **PD** =  $(1.6 + 0.6 + 5 + 1 + 1.3 + 6.6 + 0.5 + 1.5 + 3 + 1 + 3.9 + 10 + 7 + 11) * \lambda / 3 = 24.3 * \lambda = 7.2 \text{ u}$

#### Question 5:

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## INVERTER LAYOUT

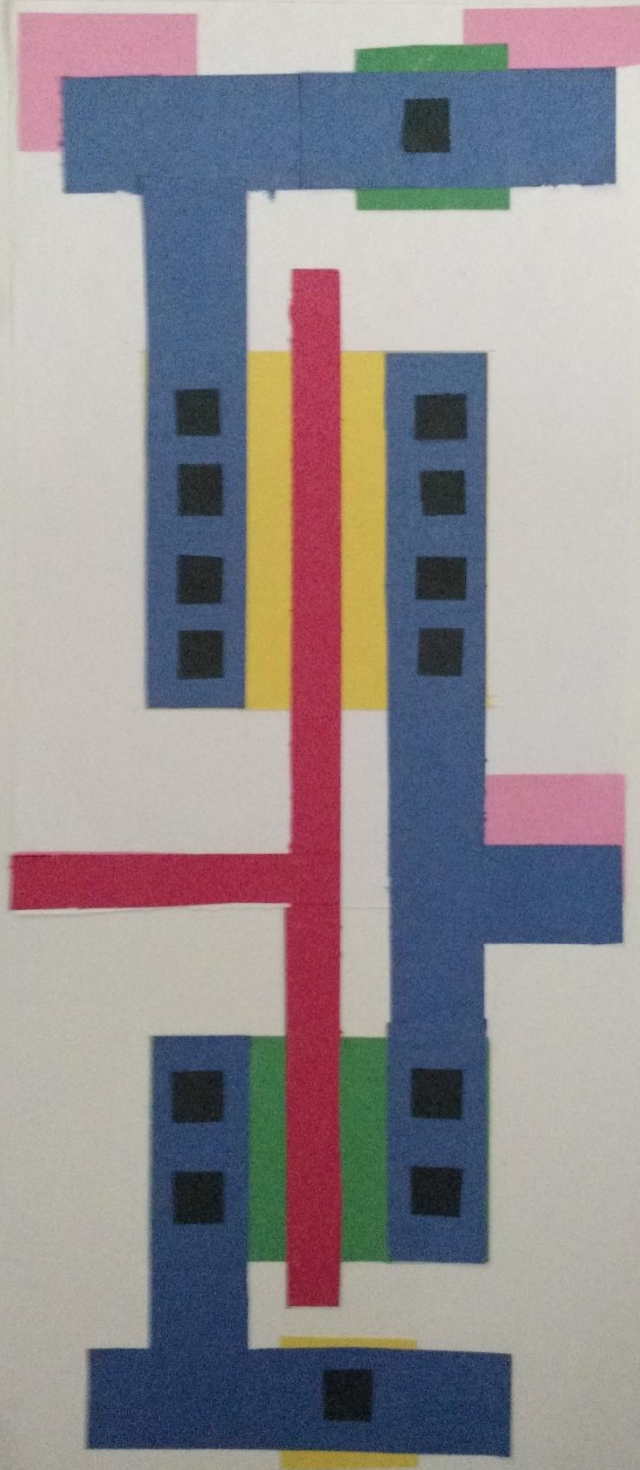


Figure 15: Layout of the inverter

For the above layout, I did not get the pink paper.

### Question 6

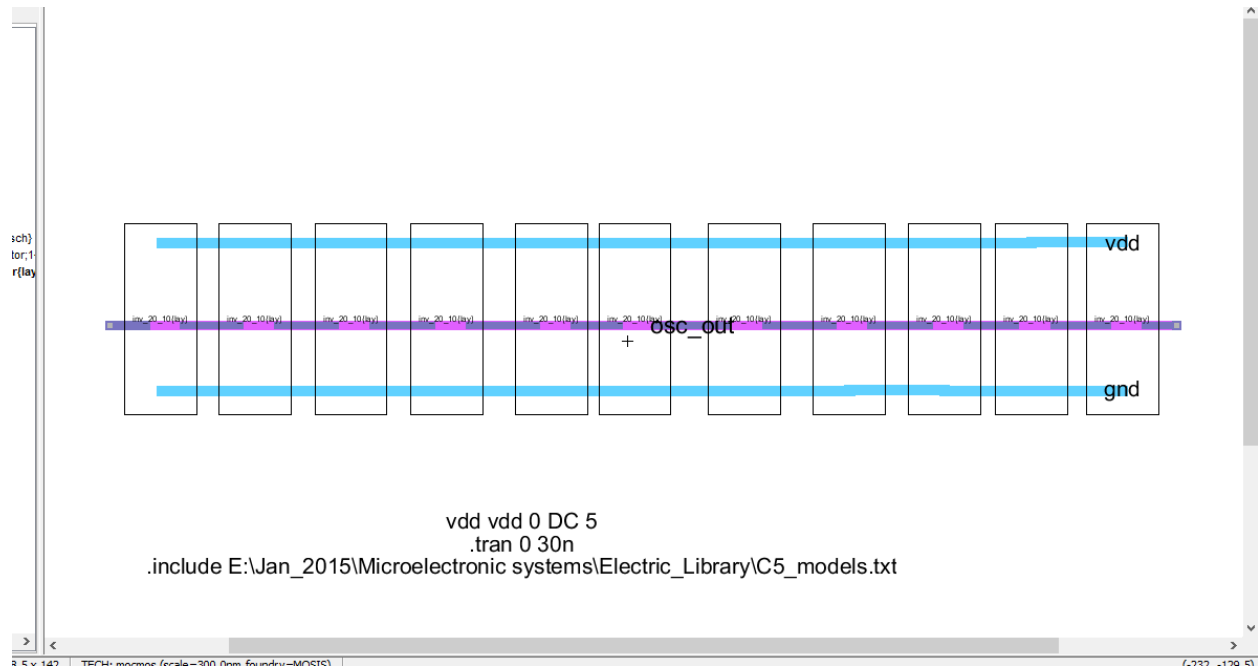


Figure 16: Layout of the ring oscillator

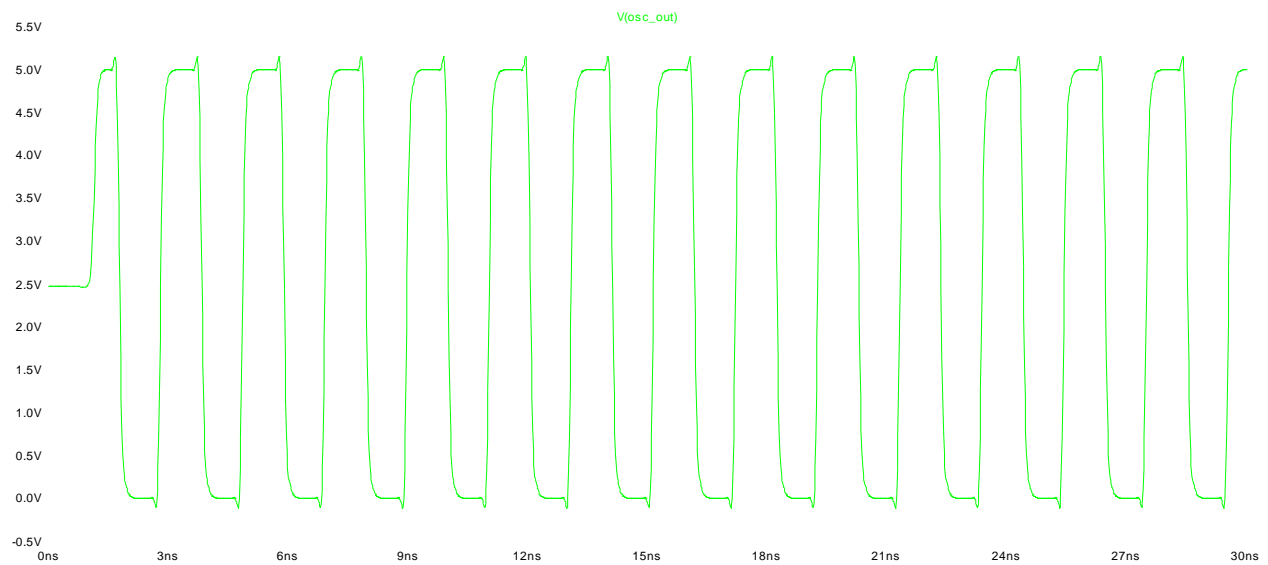


Figure 17: LTSpice output of the ring oscillator

```

*** SPICE deck for cell ring_oscillator{lay} from library tutorial_5
*** Created on Wed Mar 18, 2015 23:54:04
*** Last revised on Sat Mar 21, 2015 16:16:39
*** Written on Sat Mar 21, 2015 16:19:34 by Electric ULSI Design System,
*** version 9.05
*** Layout tech: mcomos, Foundry MOSIS
*** UC SPICE *** , MIN_RESIST 4.0, MIN_CAPAC 0.1FF

*** SUBCIRCUIT tutorial_5_inv_20_10 FROM CELL inv_20_10{lay}
.SUBCKT tutorial_5_inv_20_10 gnd in out vdd
Mnmos00 out in gnd gnd NMOS L=0.6U W=3U AS=14.67P AD=8.415P PS=24.78U
+PD=12.75U
Mpmos00 vdd in out vdd PMOS L=0.6U W=6U AS=8.415P AD=20.16P PS=12.75U
+PD=30.72U
.ENDS tutorial_5_inv_20_10

*** TOP LEVEL CELL: ring_oscillator{lay}
Xinv_20_10125 gnd net@23 net@24 vdd tutorial_5_inv_20_10
Xinv_20_10126 gnd net@24 osc_out vdd tutorial_5_inv_20_10
Xinv_20_10127 gnd osc_out net@26 vdd tutorial_5_inv_20_10
Xinv_20_10128 gnd net@22 net@23 vdd tutorial_5_inv_20_10
Xinv_20_10129 gnd net@21 net@22 vdd tutorial_5_inv_20_10
Xinv_20_10130 gnd net@20 net@21 vdd tutorial_5_inv_20_10
Xinv_20_10131 gnd net@26 net@27 vdd tutorial_5_inv_20_10
Xinv_20_10132 gnd net@27 net@28 vdd tutorial_5_inv_20_10
Xinv_20_10133 gnd net@28 net@29 vdd tutorial_5_inv_20_10
Xinv_20_10134 gnd net@30 net@20 vdd tutorial_5_inv_20_10
Xinv_20_10135 gnd net@29 net@30 vdd tutorial_5_inv_20_10

* Spice Code nodes in cell cell 'ring_oscillator{lay}'
vdd vdd 0 DC 5
.tran 0 30n
.include E:\Jan_2015\Microelectronic systems\Electric_Library\C5_models.txt
.END

```

Figure 18: Spice netlist of the ring oscillator

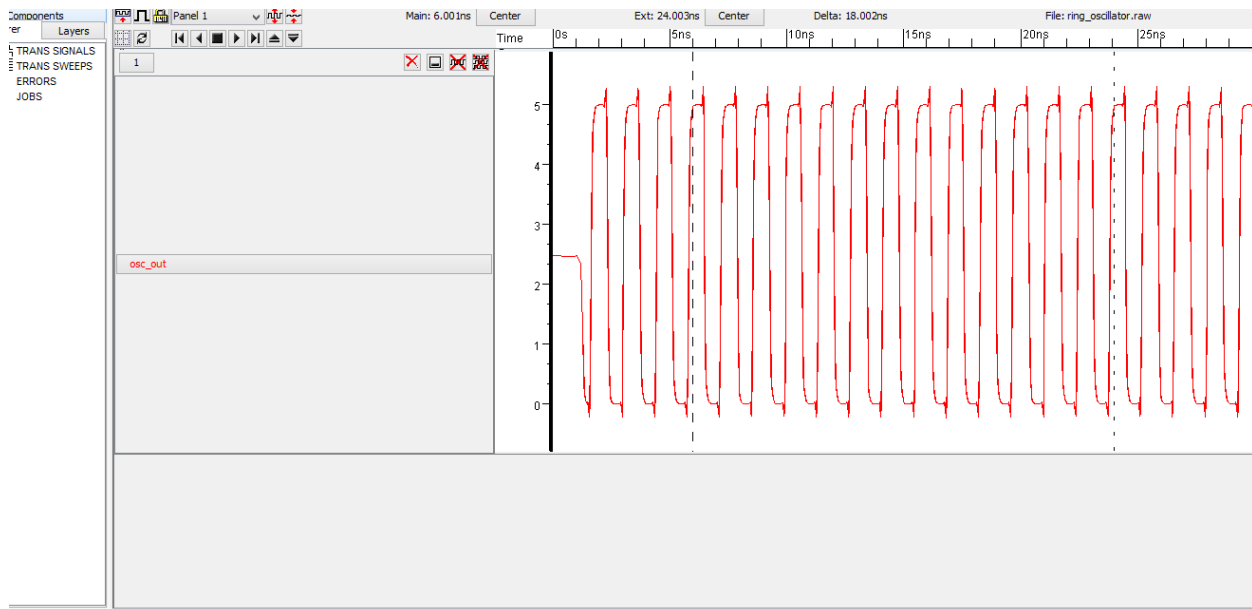


Figure 19: Electric output of the ring oscillator

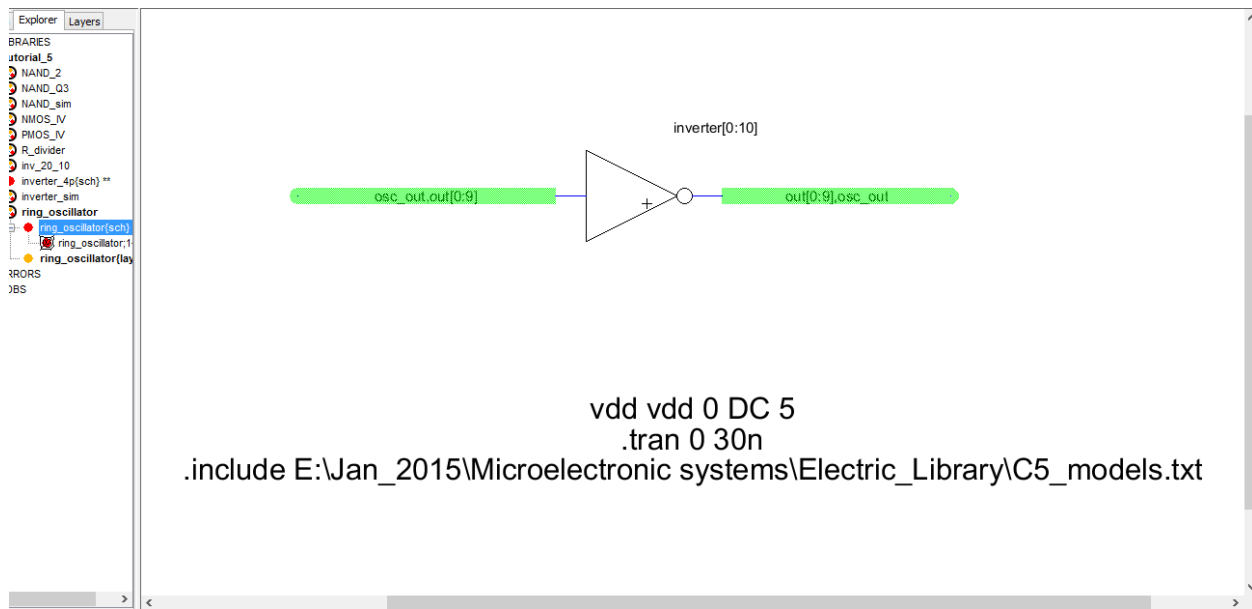


Figure 20: Ring oscillator schematic

```

*** SPICE deck for cell ring_oscillator{sch} from library tutorial_5
*** Created on Wed Mar 18, 2015 23:22:27
*** Last revised on Wed Mar 18, 2015 23:50:49
*** Written on Sat Mar 21, 2015 16:33:25 by Electric VLSI Design System,
*** version 9.05
*** Layout tech: mcmos, foundry MOSIS
*** UC SPICE *** , MIN_RESIST 4.0, MIN_CAPAC 0.1FF

*** SUBCIRCUIT tutorial_5__inv_20_10 FROM CELL inv_20_10{sch}
.SUBCKT tutorial_5__inv_20_10 in out
** GLOBAL gnd
** GLOBAL vdd
Mnmos@0 out in gnd gnd NMOS L=0.6U W=3U
Mnmos@1 out in vdd vdd PMOS L=0.6U W=6U
.ENDS tutorial_5__inv_20_10

.global gnd vdd

*** TOP LEVEL CELL: ring_oscillator{sch}
Xinverter[0] osc_out out[0] tutorial_5__inv_20_10
Xinverter[1] out[0] out[1] tutorial_5__inv_20_10
Xinverter[2] out[1] out[2] tutorial_5__inv_20_10
Xinverter[3] out[2] out[3] tutorial_5__inv_20_10
Xinverter[4] out[3] out[4] tutorial_5__inv_20_10
Xinverter[5] out[4] out[5] tutorial_5__inv_20_10
Xinverter[6] out[5] out[6] tutorial_5__inv_20_10
Xinverter[7] out[6] out[7] tutorial_5__inv_20_10
Xinverter[8] out[7] out[8] tutorial_5__inv_20_10
Xinverter[9] out[8] out[9] tutorial_5__inv_20_10
Xinverter[10] out[9] osc_out tutorial_5__inv_20_10

* Spice Code nodes in cell cell 'ring_oscillator{sch}'
vdd vdd 0 DC 5
.tran 0 30n
.include E:\Jan_2015\Microelectronic systems\Electric_Library\C5_models.txt
.END

```

Figure 21: Spice netlist of schematic

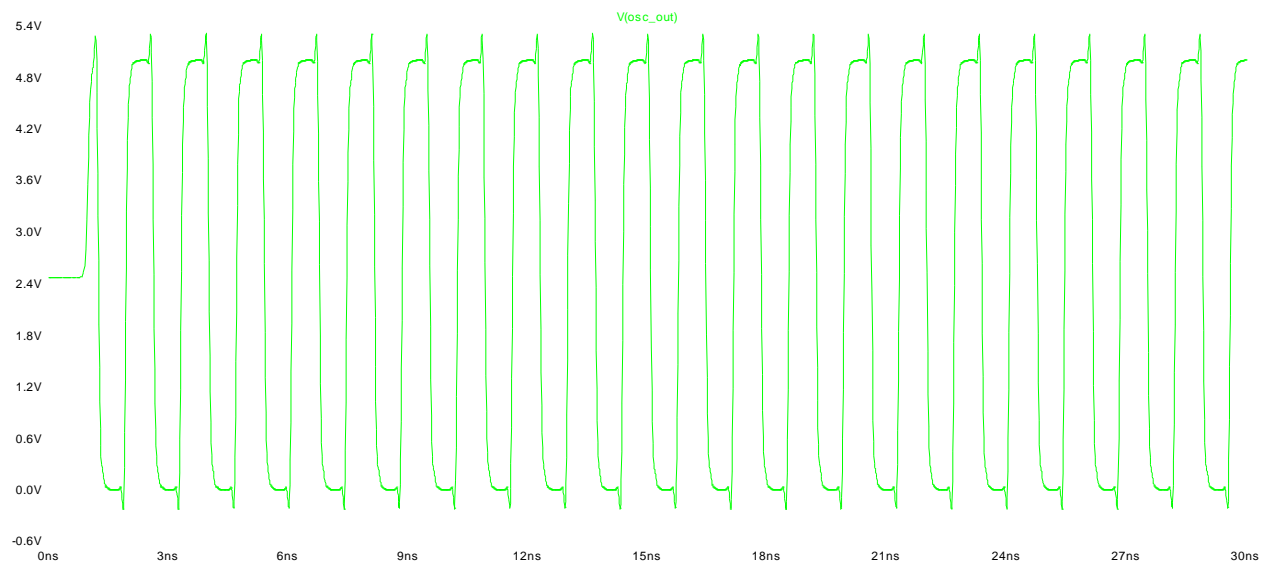


Figure 22: Spice output of the ring oscillator

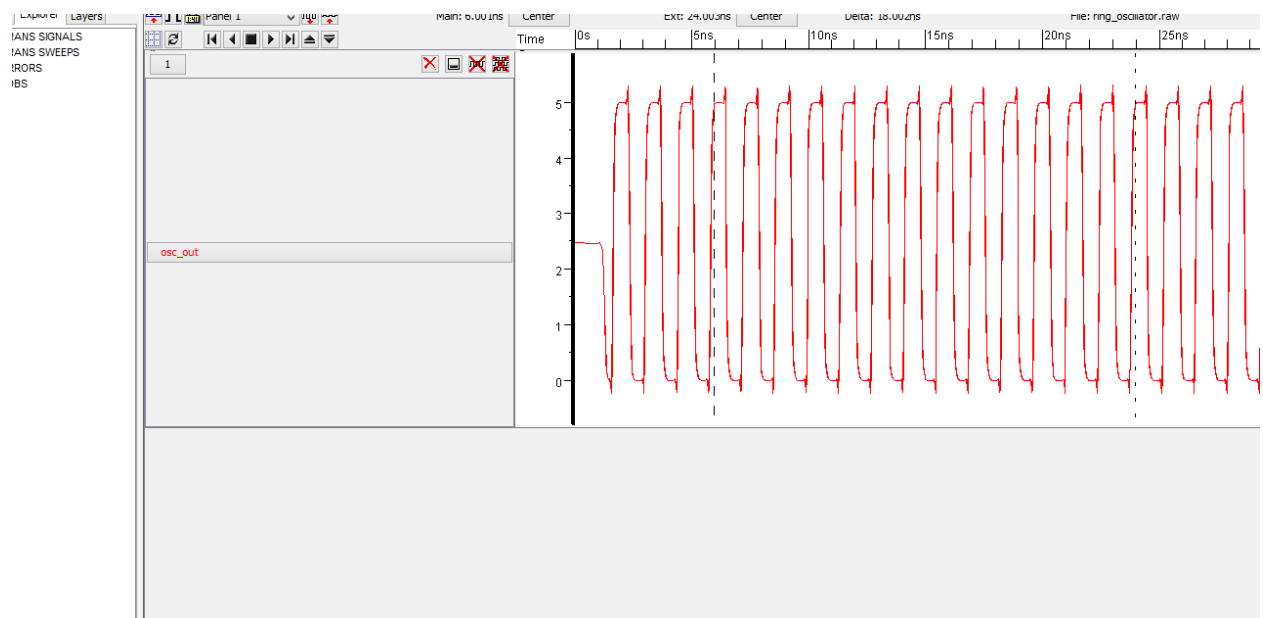


Figure 23: Electric output of the ring oscillator



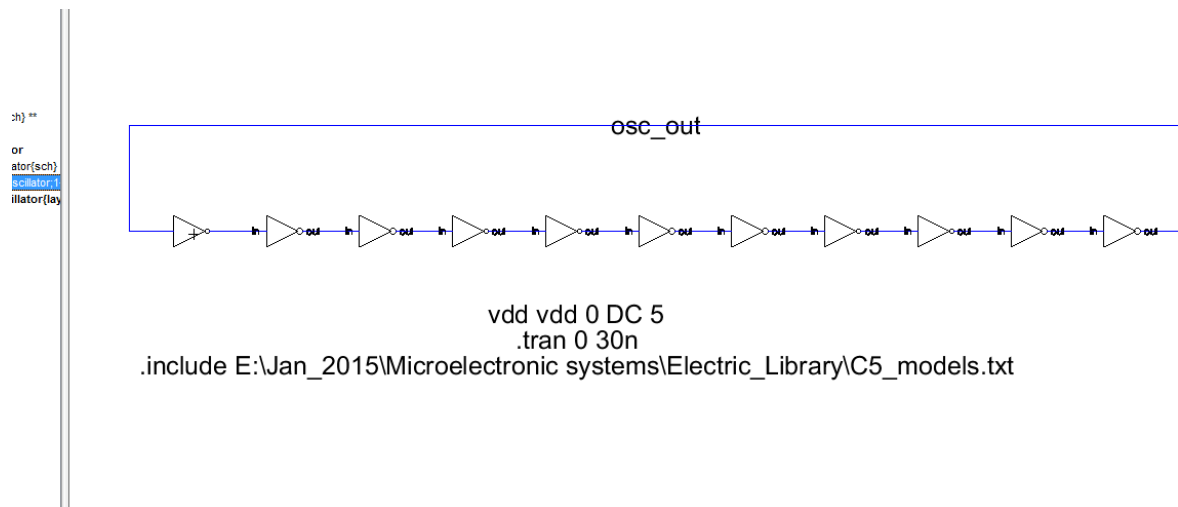


Figure 24: Ring oscillator

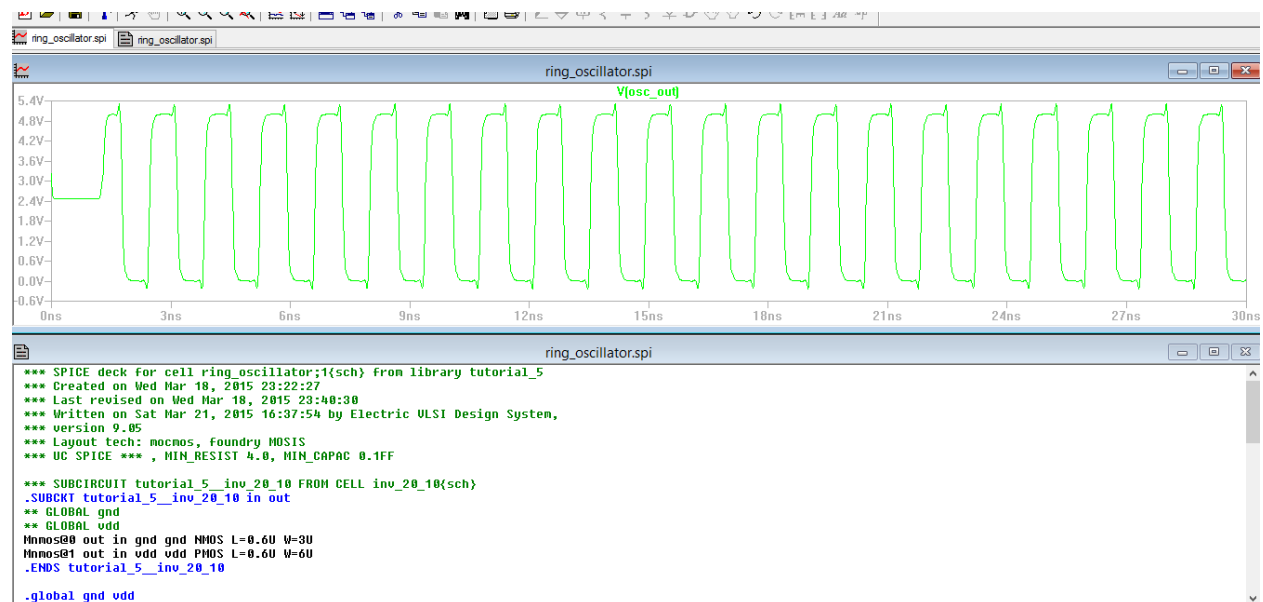


Figure 25: LTSpice output of the ring oscillator



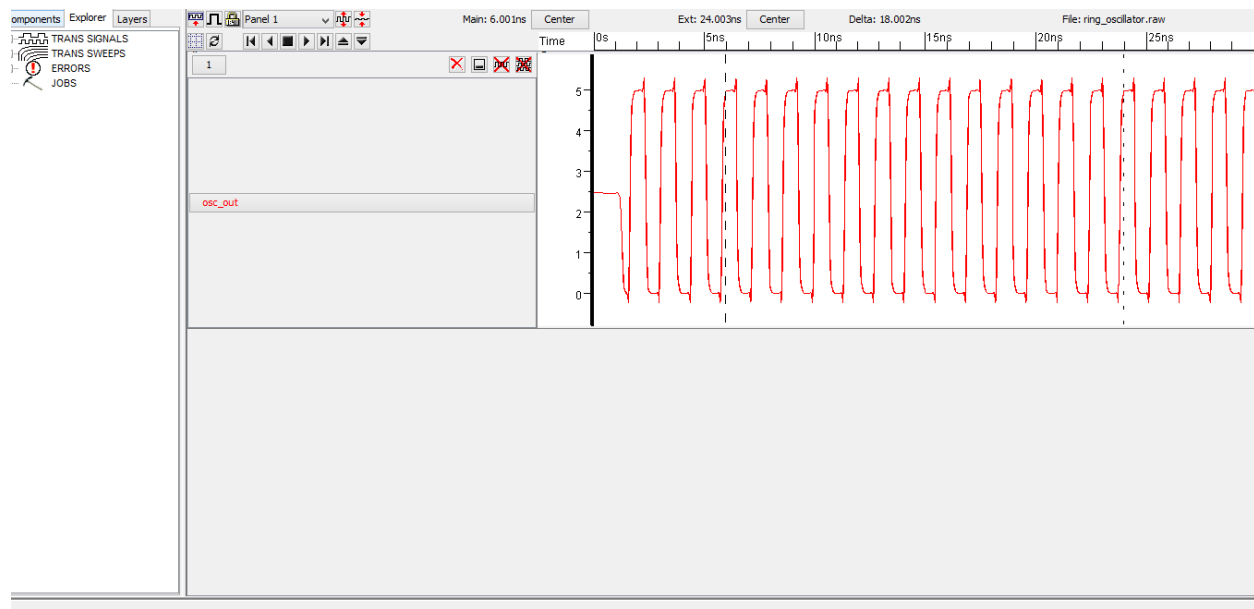


Figure 26: Electric output of the ring oscillator